

# Characterizing of MIMOSIS-1 CMOS Monolithic Active Pixel Sensor Using a 25 MeV Proton Beam at CYRCé

Ali Murteza Altingun - IPHC Strasbourg

On behalf of the IPHC-IKF-GSI  
(CBM-MVD) Collaboration

19th Apr, 2024 - 12th BTTB

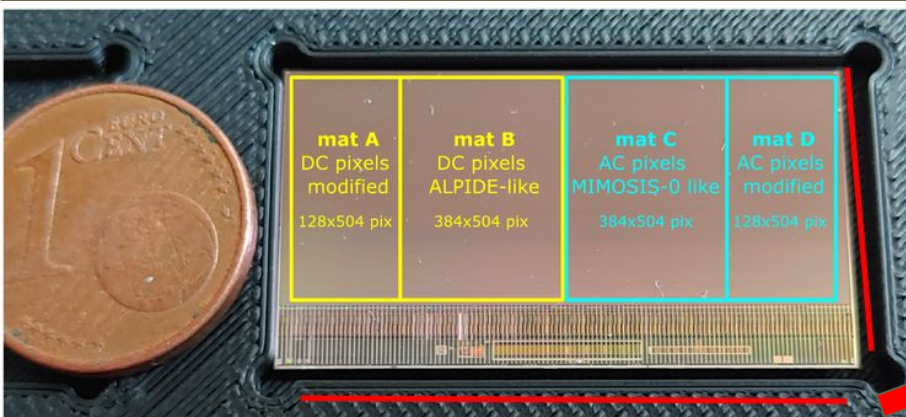


Université

de Strasbourg

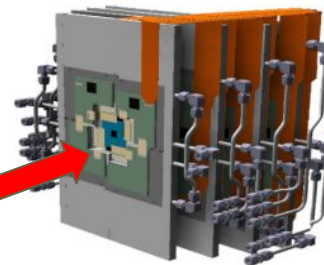


# MIMOSIS - A CMOS Sensor for CMB-MVD

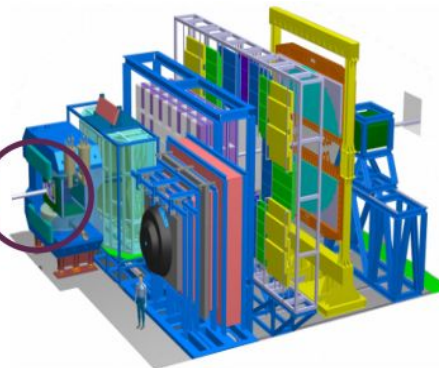


31 mm

17 mm



CBM Micro Vertex Detector (MVD)



CBM - Experiment @ FAIR

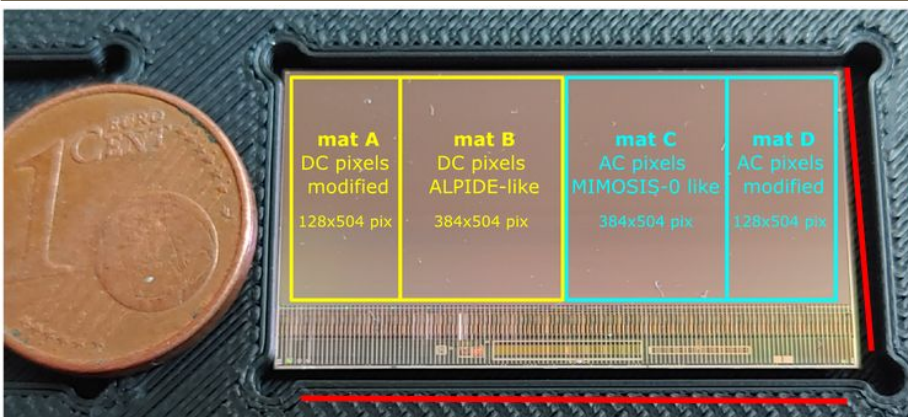
- For Micro Vertex Detector (MVD)-CBM (Compress Baryonic Matter) experiment at FAIR [1]
- MIMOSIS-1 - first full size prototype
- 1024 x 504 pixel array - size 31 x 27  $\mu\text{m}^2$

The CBM - MVD will operate at:

100 kHz Au+Au collisions @  
10 MHz p+Au collisions @  
(up to 100x higher rates in absence of MVD)



# MIMOSIS - A CMOS Sensor for CMB-MVD



31 mm

17 mm

## Parameters

Spatial/Time Res.

Sensor Thickness

Rad. Tolerance

(non-ionizing)

Rad. Tolerance

(ionizing)

Data Flow (peak hit rate)

## Requirements

~ 5  $\mu\text{m}/5 \mu\text{s}$

~ 60  $\mu\text{m}$

~  $10^{13}$  neq/cm<sup>2</sup>

~ 5 MRad

~ 70 MHz/cm<sup>2</sup>

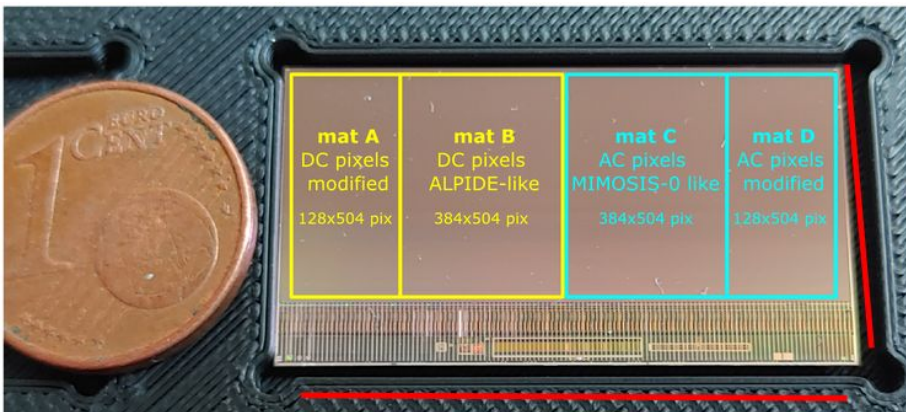
MIMOSIS pixels:

- DC-pixels → Derived from ALPIDE sensor (ALICE ITS)
- AC-pixels → foreseen improved radiation hardness with top bias possibility > 20V

4 submatrices with various pixel circuitry:

- B, C → basic pixels architectures
- A, D → 128-column matrices for analog pixel circuitry optimization

# MIMOSIS - A CMOS Sensor for CMB-MVD

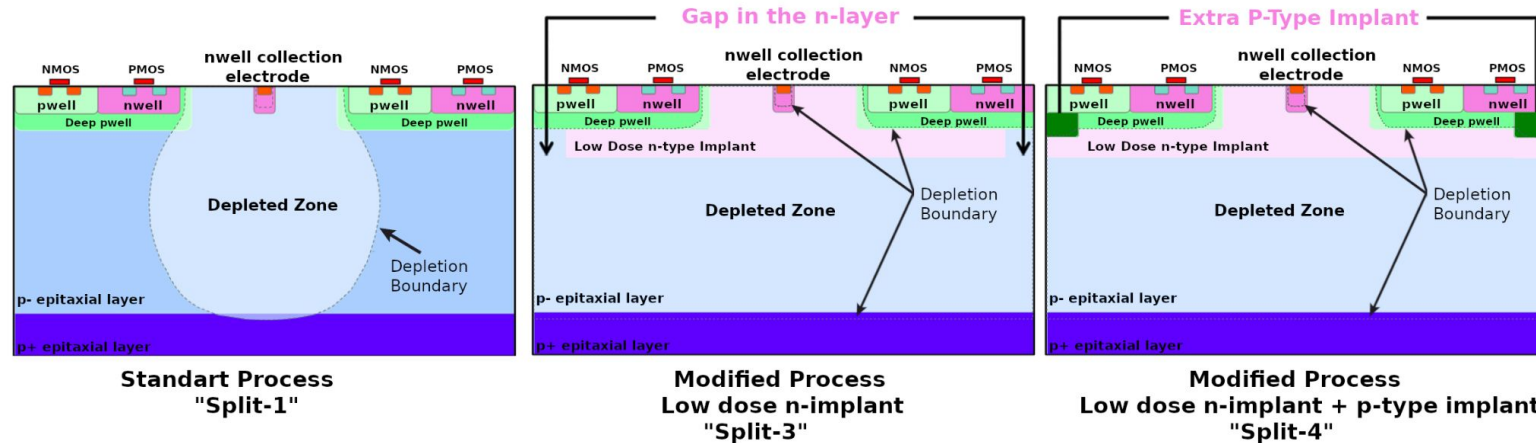


## Parameters

Spatial/Time Res.  
Sensor Thickness  
Rad. Tolerance  
(non-ionizing)  
Rad. Tolerance  
(ionizing)  
Data Flow (peak hit rate)

## Requirements

~ 5  $\mu\text{m}/5 \mu\text{s}$   
~ 60  $\mu\text{m}$   
~  $10^{13}$  neq/cm<sup>2</sup>  
~ 5 MRad  
~ 80 MHz/cm<sup>2</sup>



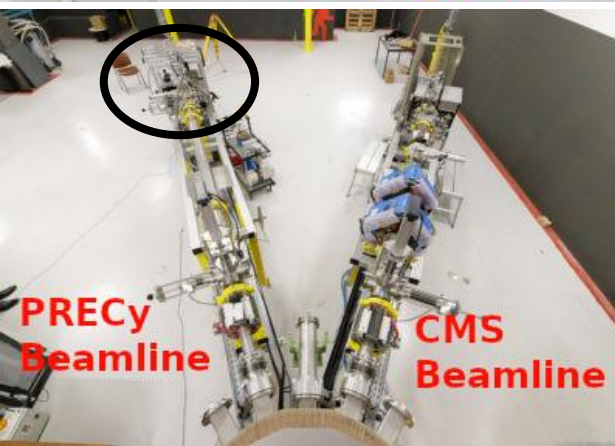
3 MIMOSIS-1 sensor type available [2]  
Standard and split-3 were investigated.



# CYRCé platform



TR24 Cyclotron

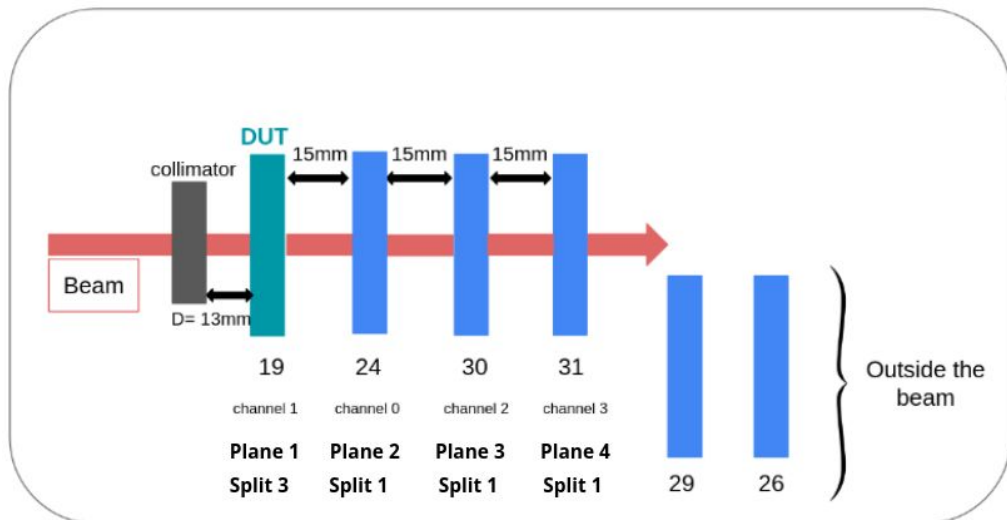


PRECy  
Beamline

CMS  
Beamline

- Radiobiology platform (PRECy Line)
  - a few keV to 25 MeV proton beams
- High particle rate capability (Intensities from 100 aA to 10 nA)
- Localized irradiations
- Testing MIMOSIS 1 chips and Cyclic proton beam characterization
- 25 MeV proton beams used (Niel factor  $\sim 1.8$ )
- Tested Split 1-3 chips with 60  $\mu\text{m}$  thickness:
  - **Different collimator sizes** (beam characterization)
  - **Threshold Scan** (study the cluster sizes and sensor efficiency)
  - **Beam Intensity Scan** (determine the limitations on data bandwidth)
  - **Testing Localized Irradiation Capability**

# Different Collimator Dimensions



**Thresh e- (DUT/Ref):** 240/120

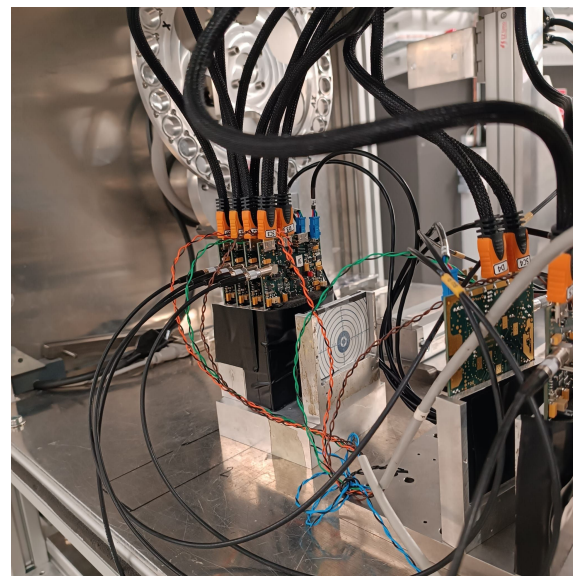
**Collimator (mm):** 2-24

**Back Bias (DUT/Ref):** -3 / -1 V

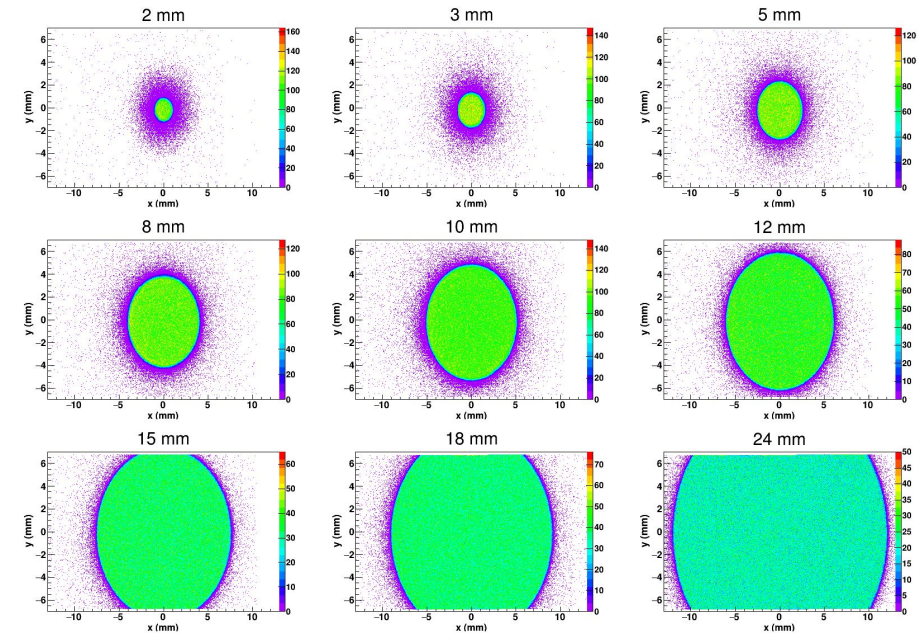
**High Voltage (DUT/Ref):** 10 / 10 V

**Chip 19 - Split 3**

- The tests for different collimators with 2-24 mm diameter
- Using a telescope of 4 planes for tracking:



# Different Collimator Dimensions - Beam Profile



- Intensity from Cyréc ( $I_C$ ):

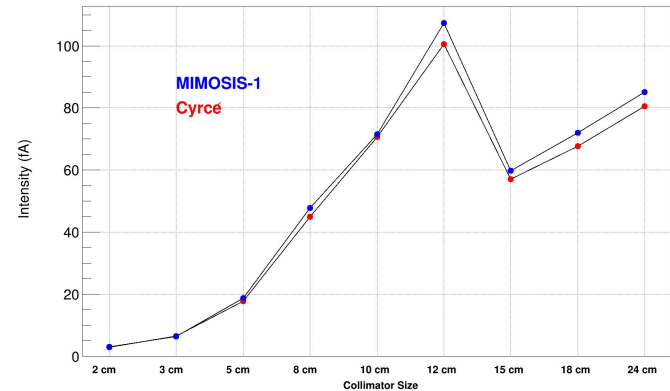
$$I_C = I_F \times a$$

( $I_F$ : Faraday cup intensity,  $a$ : geometrical factor)

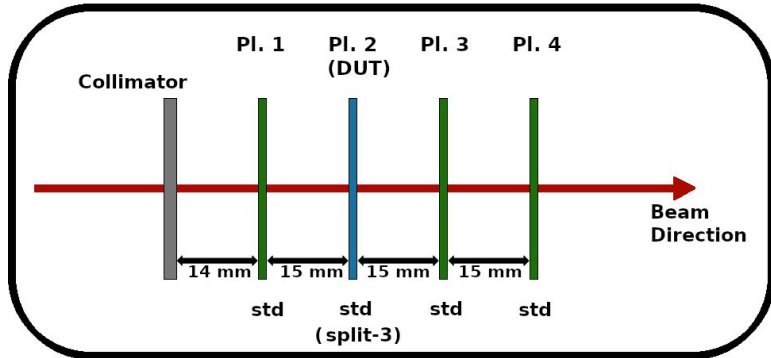
- MIMOSIS intensity

$$I_M = \frac{N \times q}{T}$$

Expected (Cyréc) vs Measured (MIMOSIS) Intensities

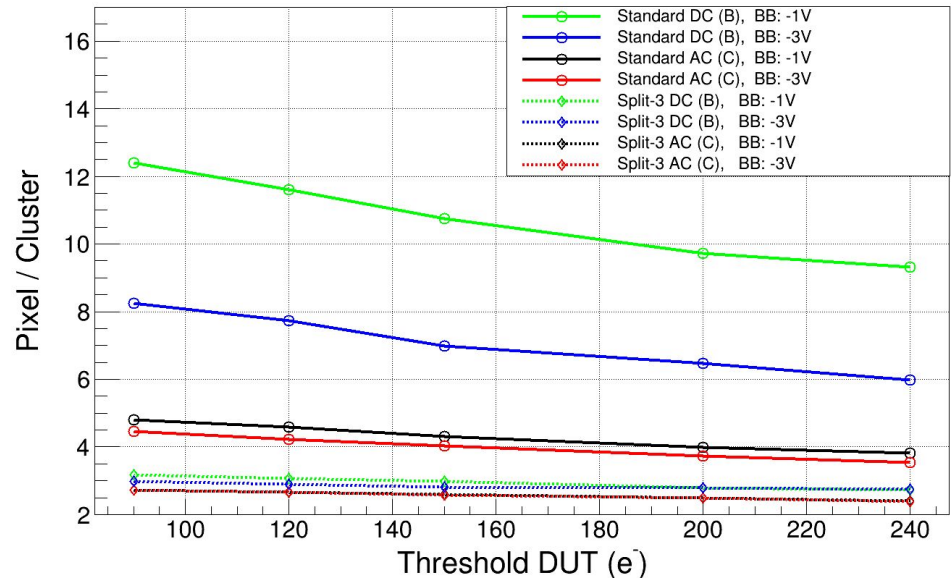


# Threshold Scan



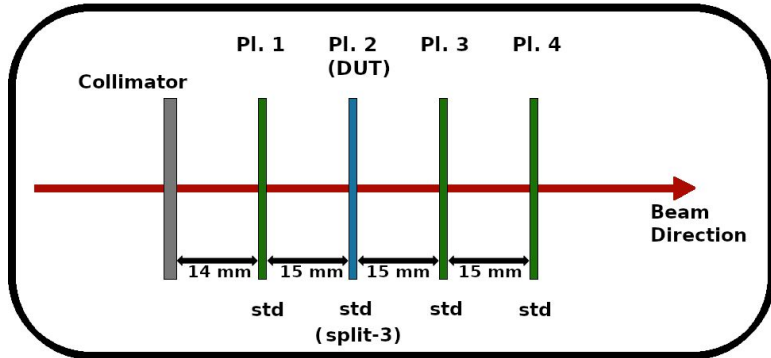
- **Threshold (e<sup>-</sup>) - (DUT):** 90 - 120 - 150 - 200 - 240, (Ref):120
- **Collimator (mm):** 10
- **DUT BB:** -3 V and -1 V, Ref
- **Planes BB:** -1 V,
- **HV:** 10 V

Average Pixel Multiplicity vs DUT Thresholds





# Threshold Scan

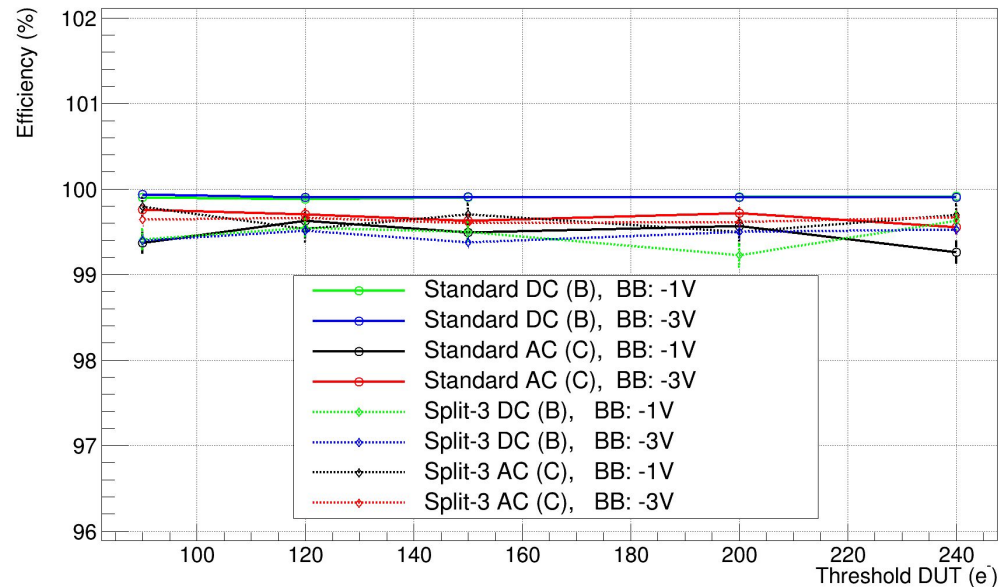


- **Threshold (e-) - (DUT):** 90 - 120 - 150 - 200 - 240, (Ref):120
- **Collimator (mm):** 10
- **DUT BB:** -3 V and -1 V, Ref
- **Planes BB:** -1 V,
- **HV:** 10 V

Track selection quality determines efficiency performance:

$$\text{Eff} = N_{\text{Track-DUT}} / N_{\text{Total-Track}}$$

Efficiency vs DUT Thresholds

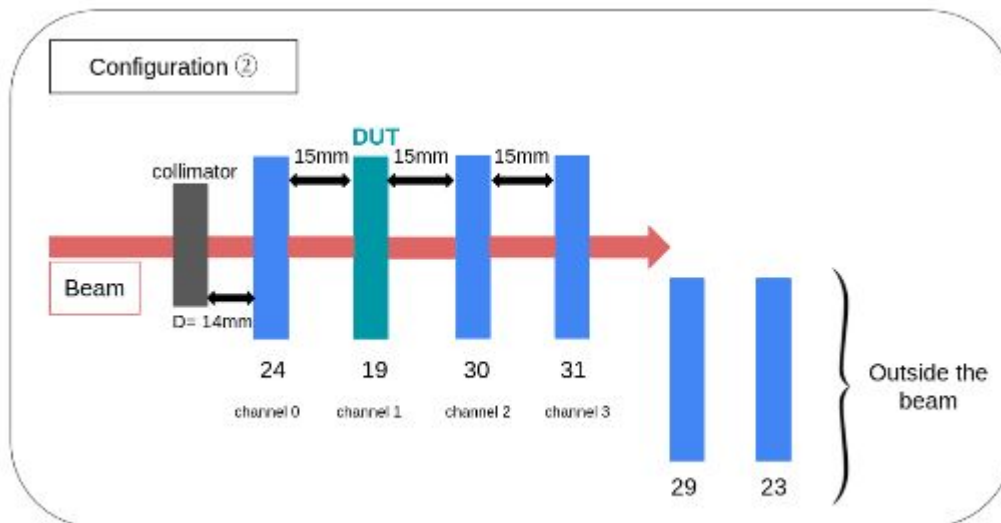


# Beam Intensity Scan

## Standard

$I_{AC}$  (pA)    $I_{DC}$  (pA)

0.04	0.04
0.07	0.07
0.30	0.29
0.59	0.59
1.16	1.15
1.74	1.72
2.32	2.31
2.88	2.88



**Thresh e- (DUT/Ref): 240/120**

**Collimator (mm): 10**

**Back Bias (DUT/Ref): -3 / -1 V**

**High Voltage (DUT/Ref): 10 / 10 V**

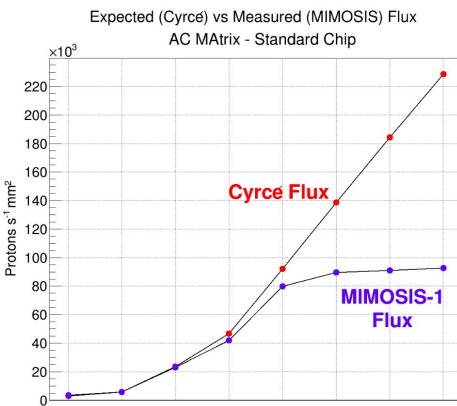
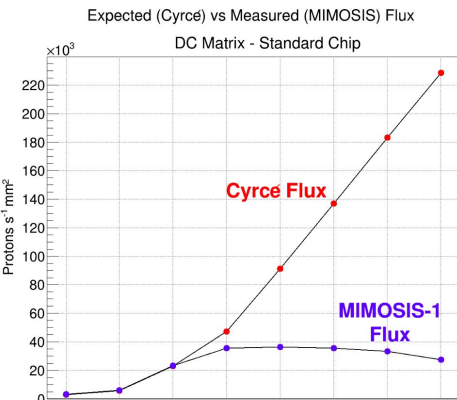
## Split-3

$I_{AC}$  (pA)    $I_{DC}$  (pA)

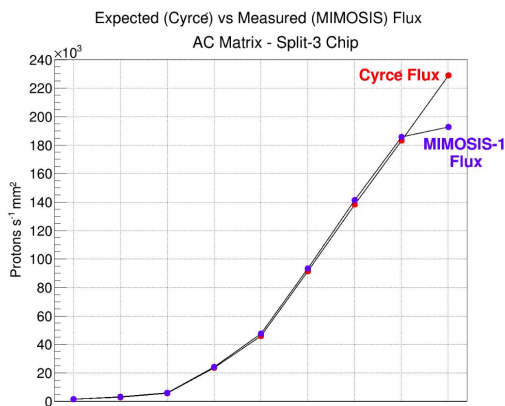
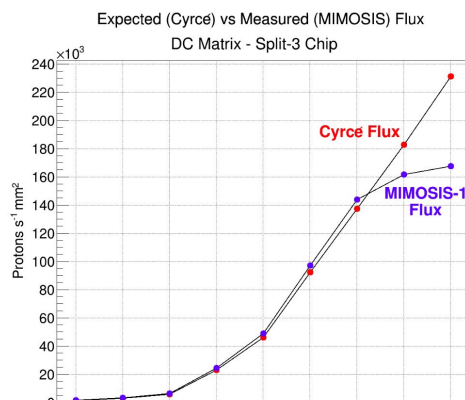
0.04	0.04
0.07	0.07
0.30	0.29
0.58	0.58
1.15	1.16
1.74	1.73
2.30	2.30
2.88	2.91

# Beam Intensity Scan

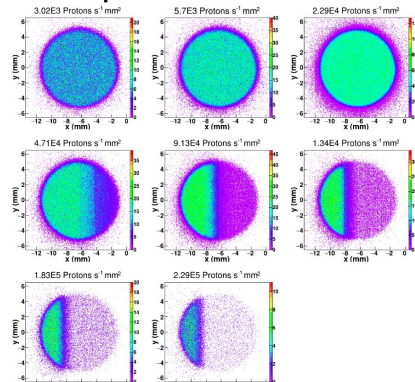
## Standard Chip



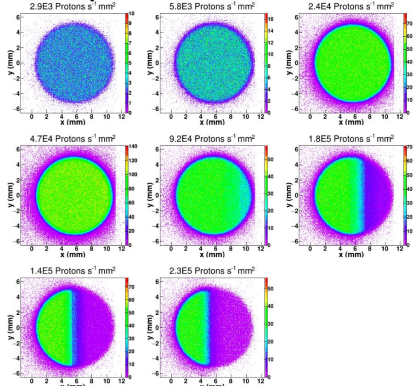
## Split-3



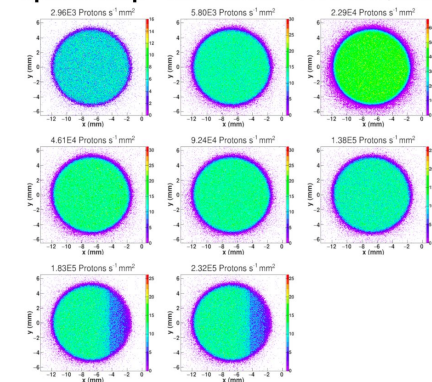
## Std Chip - DC Matrix ~ 23 kHz/mm<sup>2</sup>



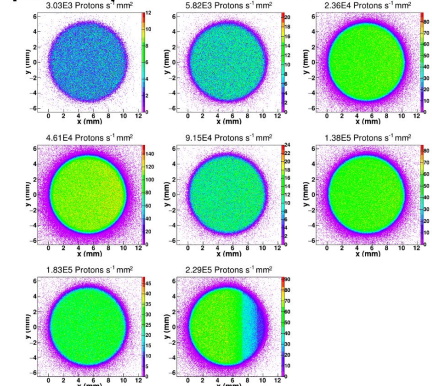
## Std Chip - AC Matrix ~ 80 kHz/mm<sup>2</sup>



## Split-3 Chip - DC Matrix ~140 kHz/mm<sup>2</sup>

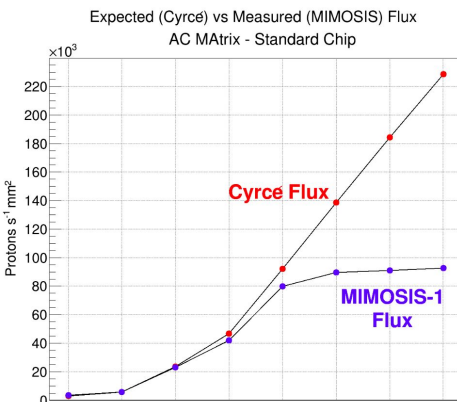
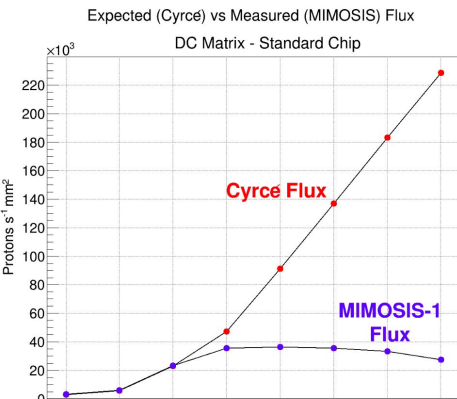


## Split-3 Chip - AC Matrix ~180 kHz/mm<sup>2</sup>

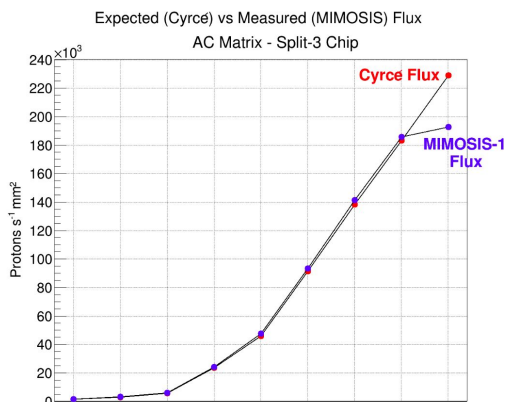
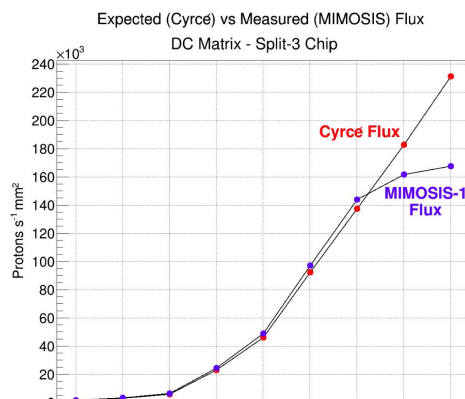


# Beam Intensity Scan

## Standard Chip



## Split-3

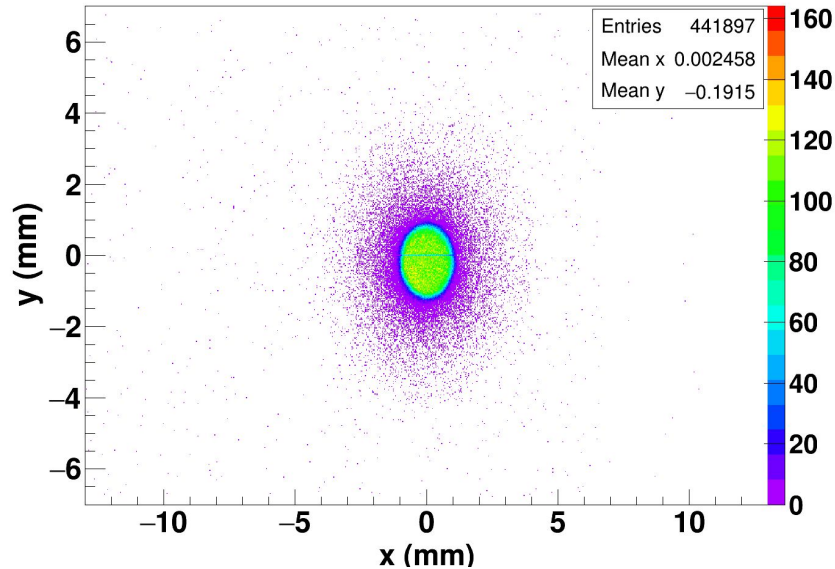


- Saturation level depends on the cluster multiplicity (size) as expected.
- Max bandwidth at around **18 MHz/cm<sup>2</sup>**
- There is 2 outputs out of 8 used on the chips.  
→ Max: 18 MHz/cm<sup>2</sup> X 4 = **72 MHz/cm<sup>2</sup>**
- Standard:
  - DC matrix ~ 10 MHz/cm<sup>2</sup>
  - AC matrix ~ 32 MHz/cm<sup>2</sup>
- Split-3:
  - DC matrix ~ 56 MHz/cm<sup>2</sup>
  - AC matrix ~ 72 MHz/cm<sup>2</sup>
  - Requirement ~ 70 MHz/cm<sup>2</sup>[1]



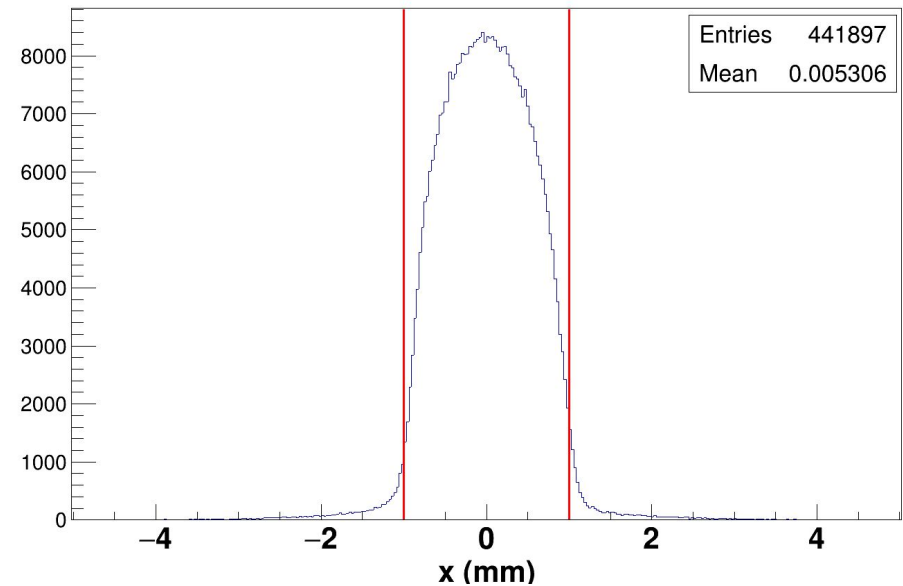
# Localized Radiation at Cyr c  - Proton beam with 2 mm

2 mm



- Proton beam (2.9 fA - 5761.5 protons/s/cm<sup>2</sup>)
- Localized irradiation verified.

2 mm



- Radiation hardness and inhomogeneous radiation field experiments for the future tests (for MIMOSIS-2)

# Summary

- The measured intensity values from sensors and the intensities from CYRCé in a good agreement.
- Further analysis ongoing for beam dispersion and fluence profile studies.
- Sensor shows expected response to high particle rates up to its data bandwidth limit. Preliminary bandwidth limit as observed for 25 MeV protons (upscaled to 8 outputs):
- Split 1 (Standard):
  - DC matrix 12 MHz/cm<sup>2</sup>
  - AC matrix 16 MHz/cm<sup>2</sup>
- Split 3:
  - DC matrix 56 MHz/cm<sup>2</sup>
  - AC matrix 72 MHz/cm<sup>2</sup> - Requirement 70 MHz/cm<sup>2</sup>
- As threshold increases, cluster multiplicity decreases slightly
- Efficiency > 99 for all thresholds
- The cluster size basically depends on the depletion.
- 25 MeV protons create larger clusters than that of MIPs
- Localized irradiation validated at CYRCé.
- Bandwidth studies can be performed at CYRCé.
- CYRCé facility is very flexible and proficient to test our sensors.

**THANK YOU!**

# References

1 - P. Klaus, M. Koziel, J. Michel, C. Muentz, J. Stroth, M. Deveaux, Technical Design Report for the CBM: Micro Vertex Detector (MVD), 310 Technical Report GSI-2022-00549, CBM Collaboration, 2022.

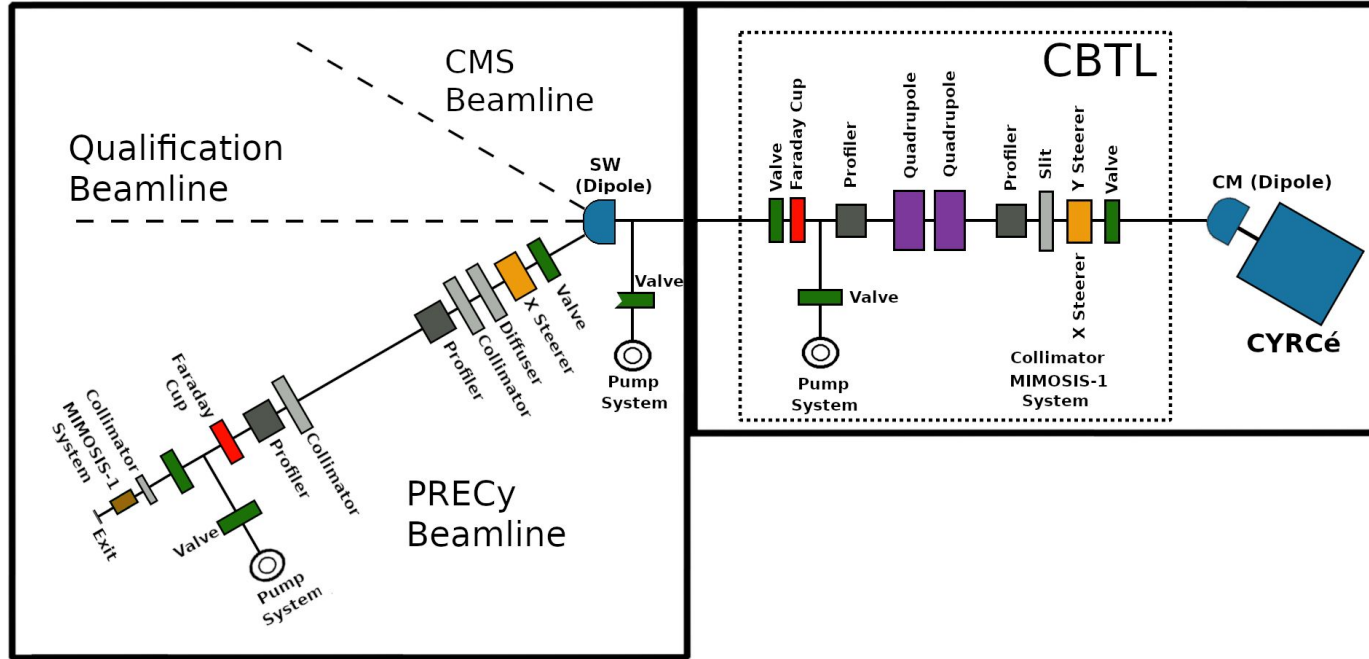
<https://repository.gsi.de/record/246516/>

2. W. Snoeys, “FASTPIX: sub-nanosecond radiation tolerant CMOS pixel sensors”, ATTRACT



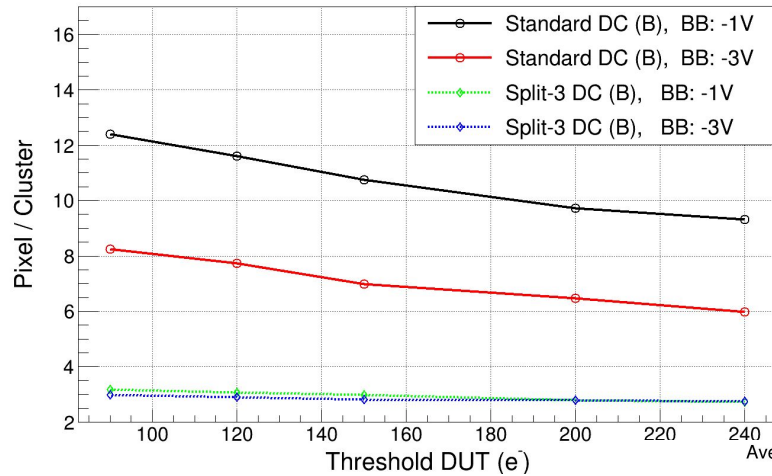
# Backup

## CYRCé

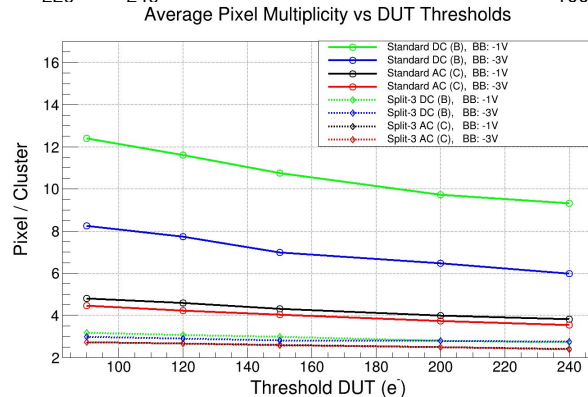
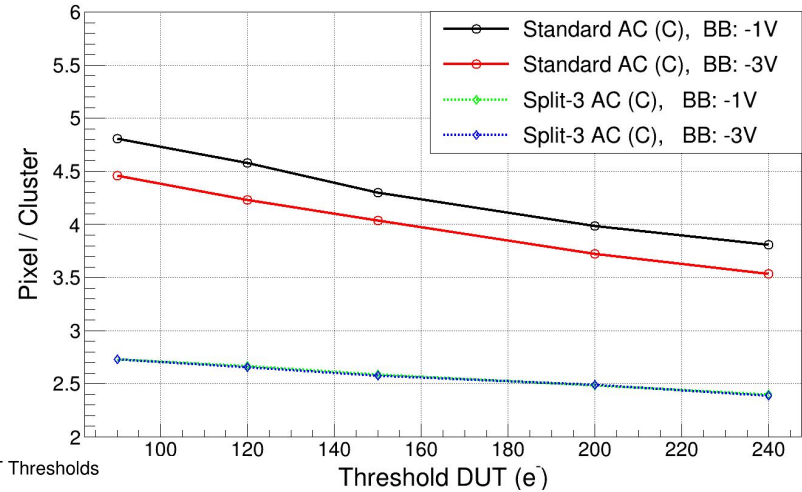


# Backup

Average Pixel Multiplicity vs DUT Thresholds



Average Pixel Multiplicity vs DUT Thresholds

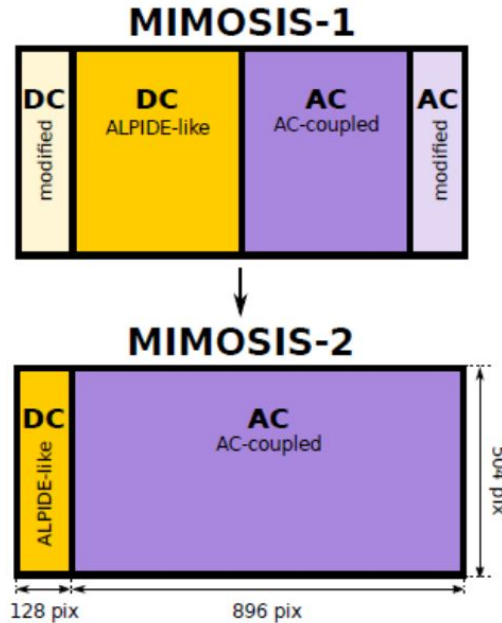


# Backup



## MIMOSIS-2:

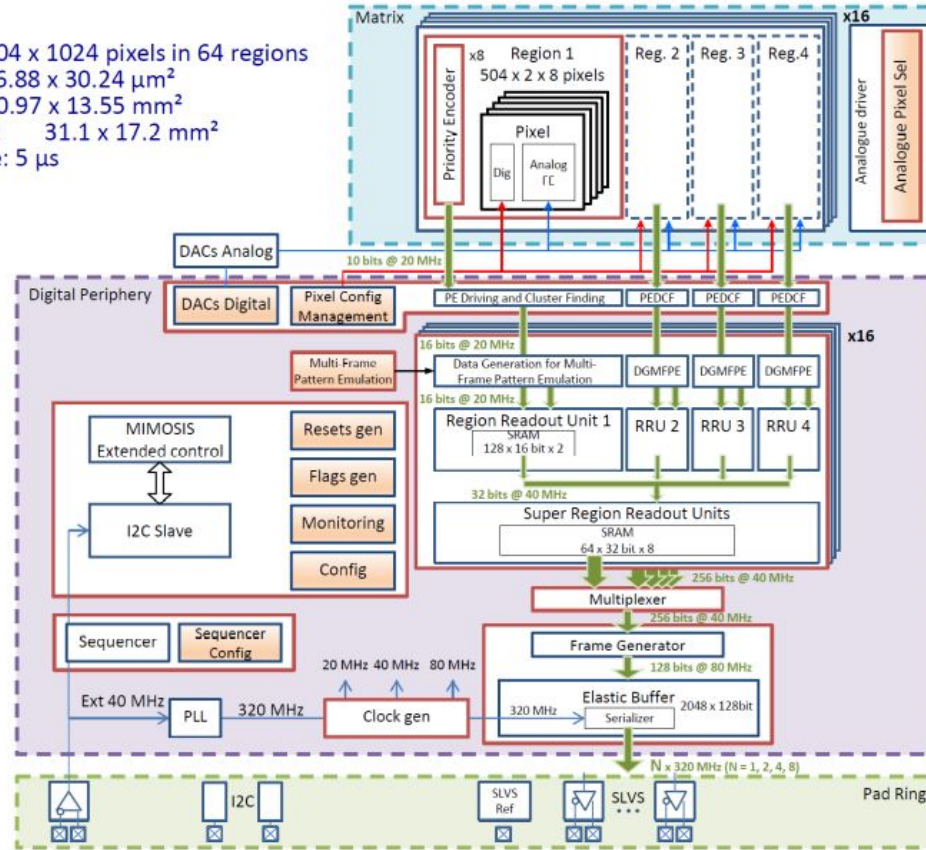
- On-chip clustering
- Additional features for SEE correction
- Various bug fixes and improvements



# Backup

- Pixel array: 504 x 1024 pixels in 64 regions
- Pixel pitch: 26.88 x 30.24  $\mu\text{m}^2$
- Active area: 30.97 x 13.55  $\text{mm}^2$
- Chip dimension: 31.1 x 17.2  $\text{mm}^2$
- Integration time: 5  $\mu\text{s}$

- Pixel array:
  - Analog part of pixel similar to ALPIDE, but 2 versions
  - Digital part of pixel redesigned
  - Priority encoder: same
- Fully reworked digital part





# Backup

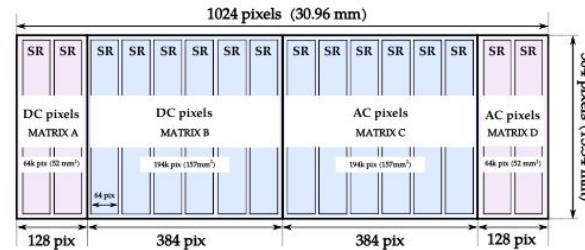
Parameter	Value
Technology	TowerJazz CIS 180 nm
Epitaxial layer	$\sim 25 \mu\text{m}$ , $> 1k\Omega\cdot\text{cm}$
Sensor thickness	$300 \mu\text{m}$ or $60 \mu\text{m}$
Pixel size	$26.9 \mu\text{m} \times 30.2 \mu\text{m}$
Pixel array	$1024 \times 504$ pixels
Sensitive area	$\approx 4.2 \text{ cm}^2$
Array readout time	$\approx 5 \mu\text{s}$
Power consumption	$< 100 \text{ mW}/\text{cm}^2$

## MIMOSIS pixels:

- **DC-pixels** → ALPIDE-like
- **AC-pixels** → foreseen improved radiation hardness with top bias possibility  $> 20V$

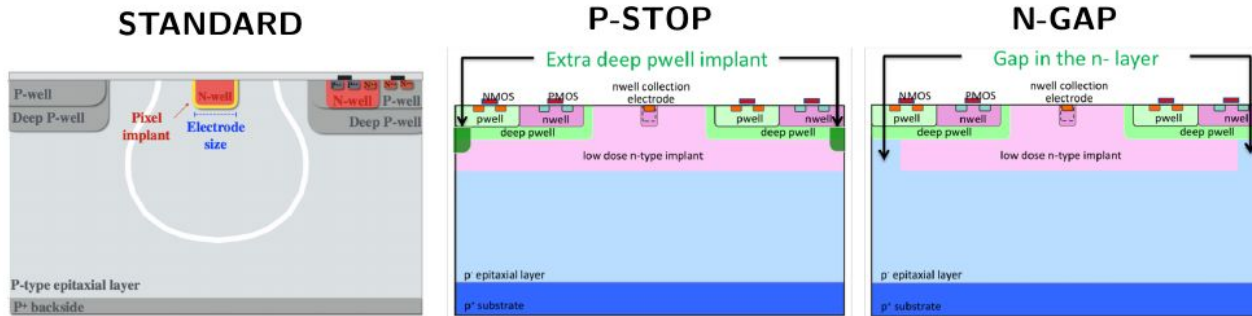
## 4 submatrices with various pixel circuitry:

- **B, C** → basic pixels architectures
- **A, D** → 128-column matrices for analog pixel circuitry optimization



# Backup

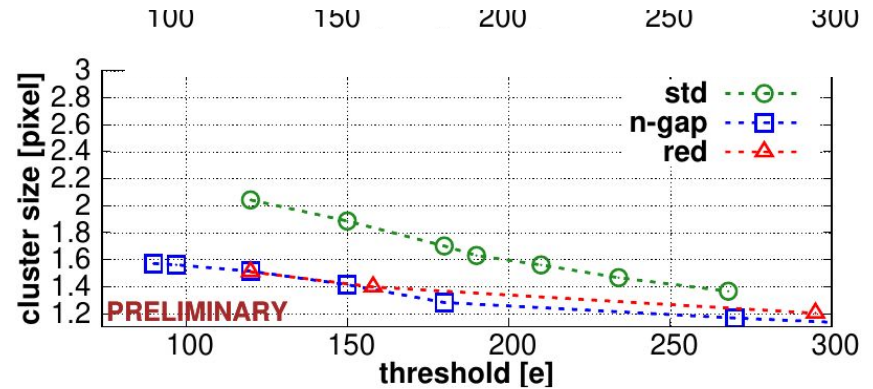
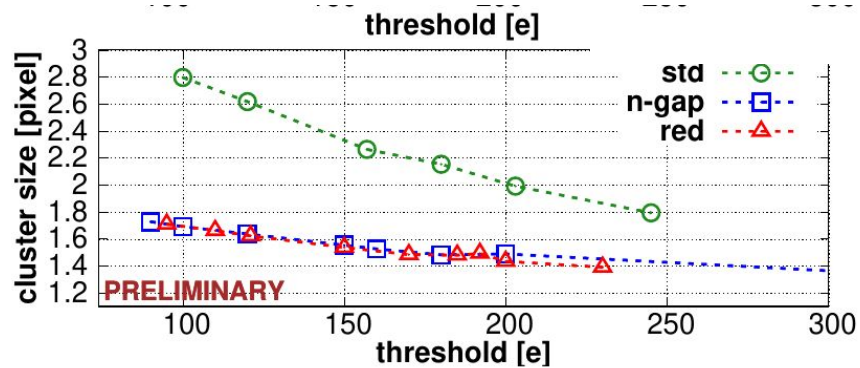
- TowerJazz CIS 180 nm technology → providing several process modifications and some flexibility on epitaxial layer thickness.
- MIMOSIS-1 available on:
  - **standard process** (3 available wafers)
  - modified process [continuous n+ layer] (3 wafers)
  - **gap in n-layer** [n-gap] (3 wafers) → expected improved radiation tolerance
  - **additional p-implant** [p-stop] (3 wafers)
- sensors 300  $\mu\text{m}$ , also thinned to  $\approx 60 \mu\text{m}$



W. Snoeys et al., NIM-A Vol.871 (2017) 90–96.  
Munker, Vertex 2018, Status of silicon detector R&D at CLIC

# Backup

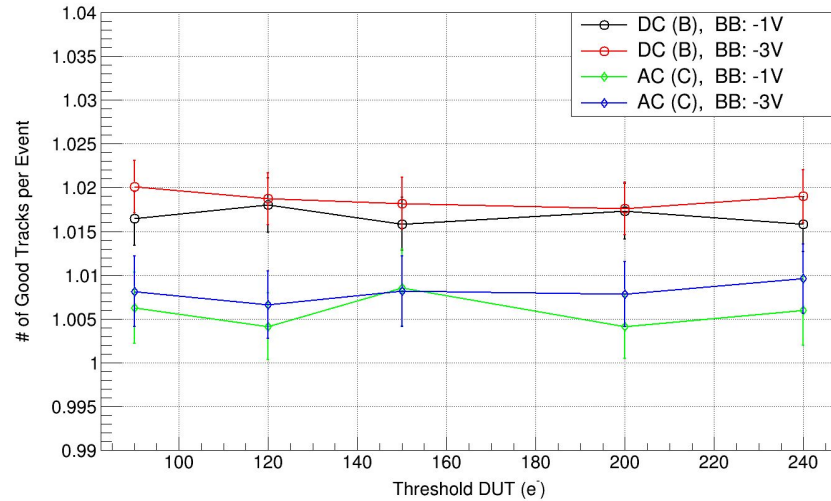
DESY -> 5 GeV e-



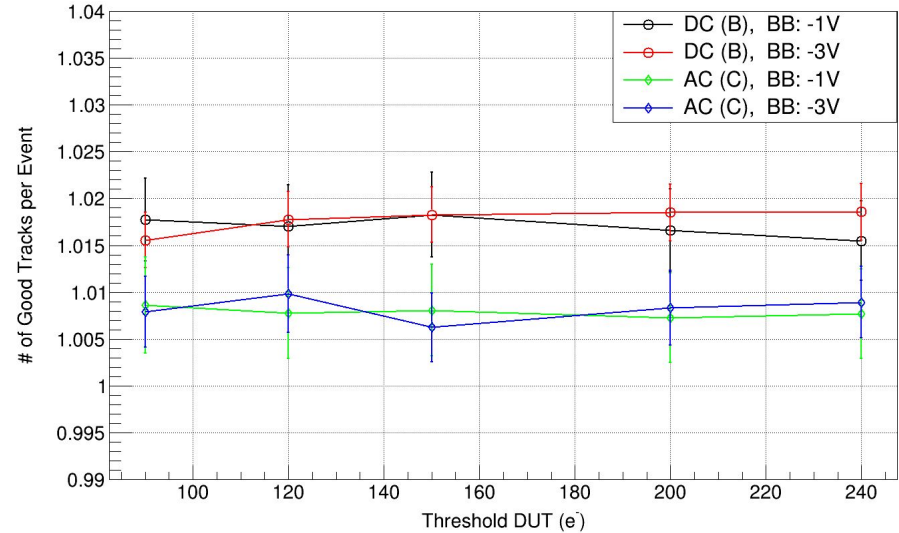
# Backup

## Track per event for Std and Split 3 chips

# of Nb of Good Rec Tracks per Event for Different DUT Thresholds- Chip 23/Split 1

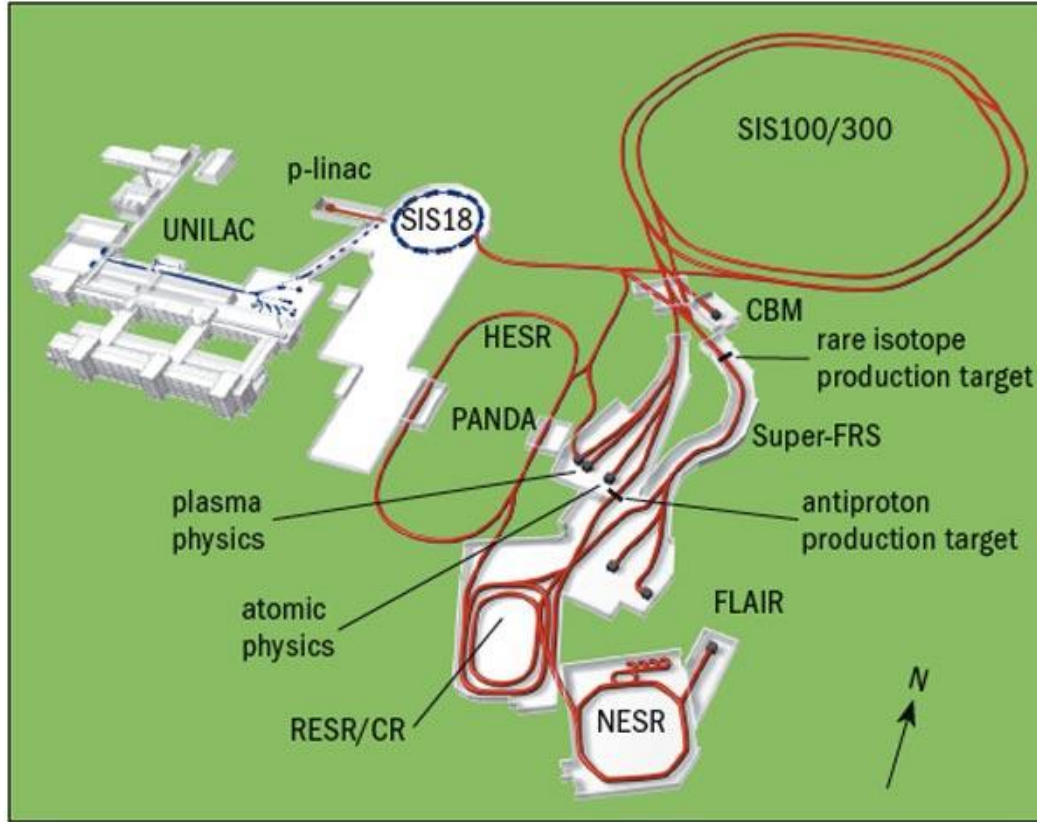


# of Nb of Good Rec Tracks per Event for Different DUT Thresholds- Chip 19/Split 3



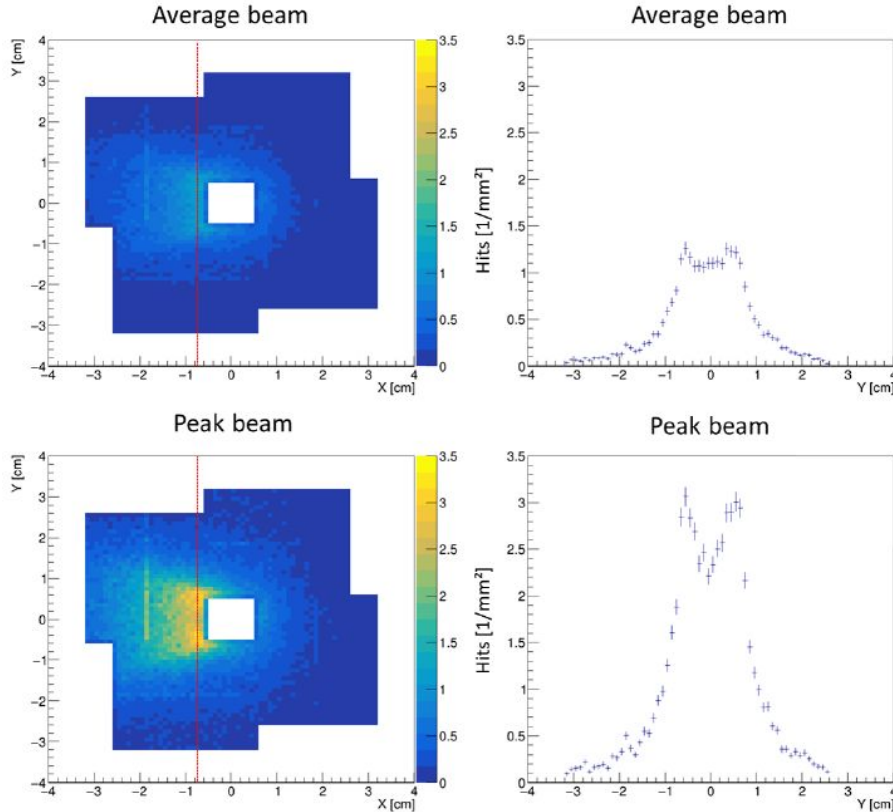


# Backup



SIS100:  
1 GeV/u Au beam  
29 GeV proton beam

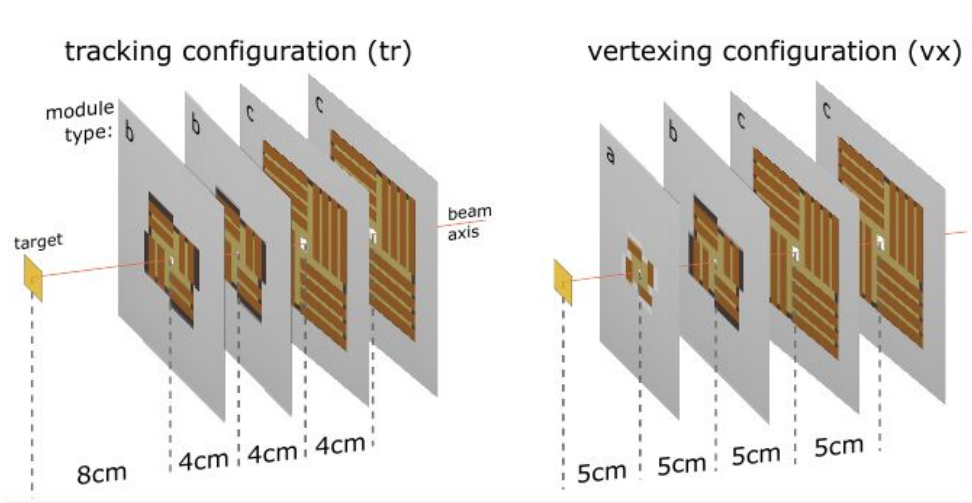
# Backup



Hit Occupancy of the first station of the MVD assuming 100 kHz Au-Au collisions at 12 AGeV beam energy and a sensor integration time of 5  $\mu$ s.

The upper panels: Values for the average occupancy, the lower panels: anticipate peak beam intensities

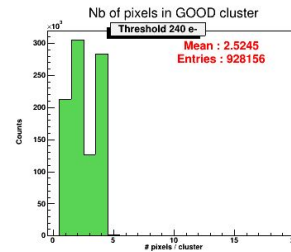
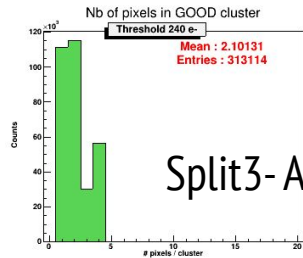
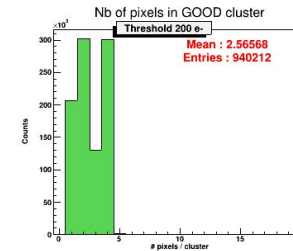
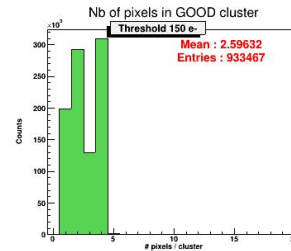
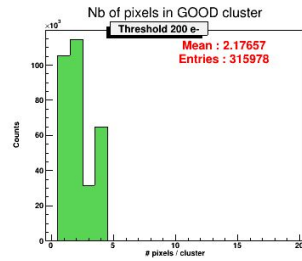
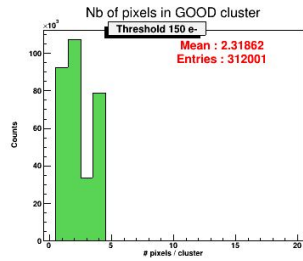
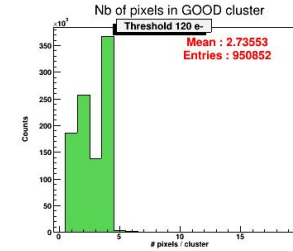
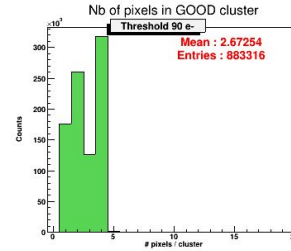
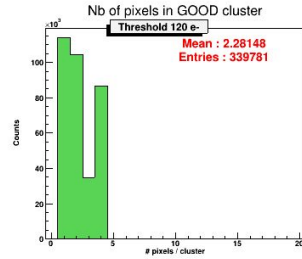
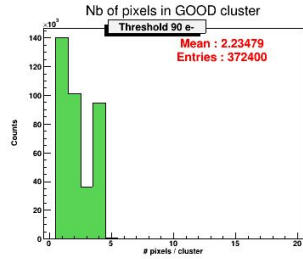
# Backup



**VX:** This geometry focuses on the identification of secondary vertices of decaying open charm D mesons

**TR:** This geometry focuses on track reconstruction of mainly low-momentum particles

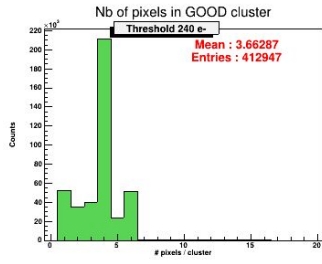
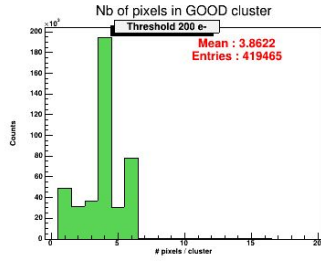
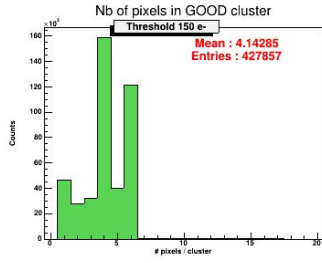
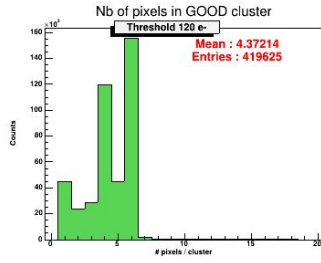
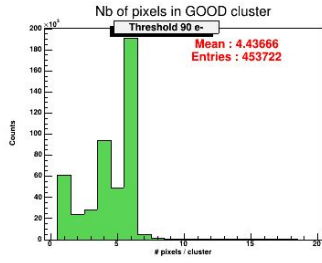
# Backup



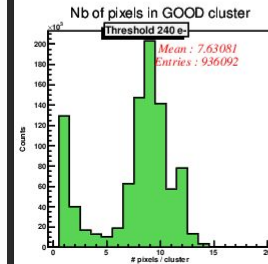
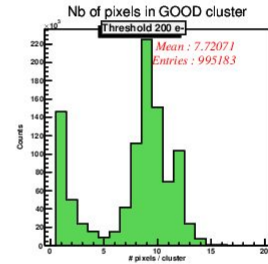
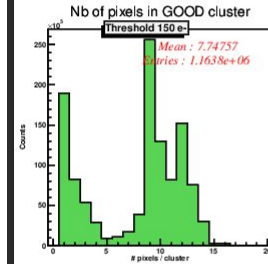
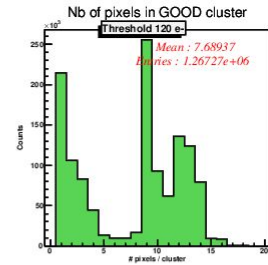
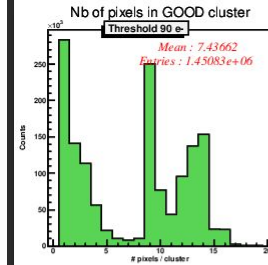
Split3- AC matrix, -1 V

Split3- DC matrix, -1 V

# Backup



Split1- AC matrix, -1 V



Split1- DC matrix, -1 V